

ABSTRACT

A semiconductor device includes a fin, a source region formed adjacent the fin and having a height greater than that of the fin, and a drain region formed adjacent the a second side of the fin and having a height greater than that of the fin. A metal gate region is formed at a top surface and at least one side surface of the fin. A width of the source and drain region may be greater than that of the fin. The semiconductor device may exhibit a reduced series resistance and an improved transistor drive current.